

Regarding the objection to the drawings, the outstanding Office Action indicates the drawing must show every feature of the invention specified in the claims and that the second well on one side of the predetermined boundary having a higher concentration than the first wells on the one side must be shown or the features cancelled from the claims. Figure 3 has been amended to include such a feature. A separate letter requesting approval of this drawing change is being submitted to the draftsman. Accordingly, it is respectfully requested this objection be withdrawn.

Regarding the rejection of Claims 16 and 23 under 35 U.S.C. § 102(b) as anticipated by Manning, Claim 16 has been amended to correspond with allowed Claim 1, except Claim 16 recites a plurality of element isolation films rather than "an element isolation film." In more detail, Claim 16 has been amended to recite that the second well is in contact with some of the first wells to provide electrical connection therebetween and is not in contact with the first wells adjacent to said some of the first wells. Accordingly, it is respectfully submitted independent Claim 16 is also allowable and the rejection of Claims 16 and 23 under 35 U.S.C. § 102(b) as anticipated by Manning is moot.

Consequently, in light of the above discussion and in view of the present amendment, the present application is believed to be in condition for allowance and an early and favorable action to that effect is respectfully requested.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Gregory J. Maier
Attorney of Record
Registration No. 25,599
David A. Bilodeau
Registration No. 42,325



22850

(703) 413-3000
Fax #: (703) 413-2220
GJM/DAB/kst

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IN THE CLAIMS

--16. (Three Times Amended) A semiconductor device comprising:

a semiconductor substrate;

a plurality of element isolation films formed such as to have a predetermined uniform depth from a main surface of said semiconductor substrate, said element isolation films dividing the area from said main surface to said depth into a plurality of first regions;

first wells formed in said first regions, respectively; and

a second well formed in a second region deeper than each of said first wells in said semiconductor substrate, said second well being in contact with some of said first wells to provide electrical connection therebetween and not being in contact with said first wells adjacent to said some of said first wells,

wherein said first and second wells of said first and second regions on one side with reference to a predetermined boundary are of a first conductivity type, and said first wells on the other side are of a second conductivity type, and

wherein said second well is formed only on one side of said second region with reference to the predetermined boundary.--

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